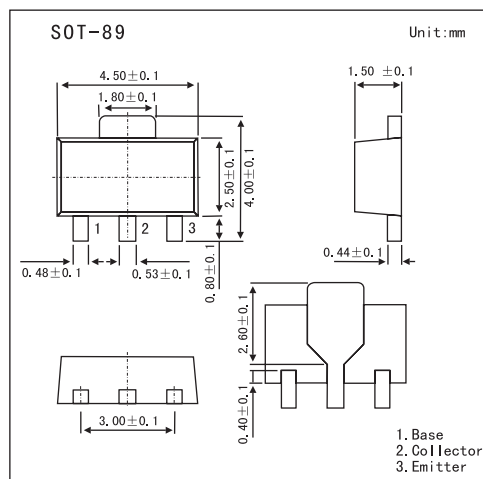


■ Features

- Low frequency power amplifier.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V <sub>CB0</sub>	100	V
Collector to emitter voltage	V <sub>CEO</sub>	50	V
Emitter to base voltage	V <sub>EBO</sub>	6	V
Collector current	I <sub>C</sub>	1	A
Peak collector current	I <sub>CP</sub> *1	1.5	A
Collector power dissipation	P <sub>C</sub> *2	1	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\*1. PW ≤ 10 ms; d ≤ 0.02.

\*2. Value on the alumina ceramic board (12.5 X 20 X 0.7 mm)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0	100			V
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 1 mA, R <sub>BE</sub> = ∞	50			V
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 10 μA, I <sub>C</sub> = 0	6			V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> = 80 V, I <sub>E</sub> = 0			0.1	μA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = 4 V, I <sub>C</sub> = 0			0.1	μA
DC current transfer ratio	h <sub>FE</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.1 A	100		500	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 1 A, I <sub>B</sub> = 0.1 A			0.3	V
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 1 A, I <sub>B</sub> = 0.1 A			1.2	V
Gain bandwidth product	f <sub>T</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 10 mA		100		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz		20		pF

■ hFE Classification

Marking	CA	CB	CC
hFE	100~200	160~320	250~500